Irina A Buyanova

List of Publications by Citations

324 papers	5,118 citations	32 h-index	58 g-index
353 ext. papers	5,598 ext. citations	4.1 avg, IF	5.17 L-index

#	Paper	IF	Citations
324	Design rules for minimizing voltage losses in high-efficiency organic solar cells. *Nature Materials*, **2018**, 17, 703-709	27	500
323	Mechanism for low-temperature photoluminescence in GaNAs/GaAs structures grown by molecular-beam epitaxy. *Applied Physics Letters*, **1999**, 75, 501-503	3.4	227
322	Electronic Properties of Ga(In)NAs Alloys. *MRS Internet Journal of Nitride Semiconductor Research*, **2001**, 6, 1		157
321	Direct determination of electron effective mass in GaNAs/GaAs quantum wells. *Applied Physics Letters*, **2000**, 77, 1843	3.4	156
320	. *IEEE Transactions on Electron Devices*, **2007**, 54, 1040-1048	2.9	121
319	Oxygen and zinc vacancies in as-grown ZnO single crystals. *Journal Physics D: Applied Physics*, **2009**, 42, 175411	3	106
318	Wide bandgap GaN-based semiconductors for spintronics. *Journal of Physics Condensed Matter*, **2004**, 16, R209-R245	1.8	106
317	Mechanism for rapid thermal annealing improvements in undoped GaNxAs1□/GaAs structures grown by molecular beam epitaxy. *Applied Physics Letters*, **2000**, 77, 2325-2327	3.4	87
316	Influence of conduction-band nonparabolicity on electron confinement and effective mass in GaNxAs1□□aAs quantum wells. *Physical Review B*, **2004**, 69,	3.3	85
315	Ferromagnetism in Transition-Metal Doped ZnO. *Journal of Electronic Materials*, **2007**, 36, 462-471	1.9	80
314	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. *Nature Materials*, **2009**, 8, 198-202	27	78
313	Time-resolved studies of photoluminescence in GaNxP1□ alloys: Evidence for indirect-direct band gap crossover. *Applied Physics Letters*, **2002**, 81, 52-54	3.4	77
312	Band gap properties of Zn1□CdxO alloys grown by molecular-beam epitaxy. *Applied Physics Letters* , **2006**, 89, 151909	3.4	71
311	Formation of nonradiative defects in molecular beam epitaxial GaNxAs1□ studied by optically detected magnetic resonance. *Applied Physics Letters*, **2001**, 79, 3089-3091	3.4	59
310	Radiative recombination mechanism in GaNxP1□ alloys. *Applied Physics Letters*, **2002**, 80, 1740-1742	3.4	59
309	Photoluminescence of GaN: Effect of electron irradiation. *Applied Physics Letters*, **1998**, 73, 2968-2970	3.4	55
308	Effect of growth temperature on photoluminescence of GaNAs/GaAs quantum well structures. *Applied Physics Letters*, **1999**, 75, 3781-3783	3.4	55

307	Dominant recombination centers in Ga(In)NAs alloys: Ga interstitials. *Applied Physics Letters*, **2009**, 95, 241904	3.4	54
306	Intrinsic optical properties of GaN epilayers grown on SiC substrates: Effect of the built-in strain. *Applied Physics Letters*, **1996**, 69, 1255-1257	3.4	53
305	Nitrogen passivation induced by atomic hydrogen: The GaP1−yNy case. *Physical Review B*, **2003**, 67,	3.3	51
304	Signature of an intrinsic point defect in GaNxAs1−x. *Physical Review B*, **2001**, 63,	3.3	50
303	Type I band alignment in the GaNxAs1−x/GaAs quantum wells. *Physical Review B*, **2000**, 63,	3.3	50
302	Analysis of band anticrossing in GaNxP1−x alloys. *Physical Review B*, **2004**, 70,	3.3	46
301	Zinc-Vacancy–Donor Complex: A Crucial Compensating Acceptor in ZnO. *Physical Review Applied*, **2014**, 2,	4.3	45
300	Hydrogen-induced improvements in optical quality of GaNAs alloys. *Applied Physics Letters*, **2003**, 82, 3662-3664	3.4	45
299	Free Excitons in GaN. *MRS Internet Journal of Nitride Semiconductor Research*, **1996**, 1, 1		43
298	Recombination processes in N-containing III–V ternary alloys. *Solid-State Electronics*, **2003**, 47, 467-475	1.7	39
297	Magneto-optical and light-emission properties of III–As–N semiconductors. *Semiconductor Science and Technology*, **2002**, 17, 815-822	1.8	39
296	Dilute Nitride Nanowire Lasers Based on a GaAs/GaNAs Core/Shell Structure. *Nano Letters*, **2017**, 17, 1775-1781	11.5	36
295	Er/O and Er/F doping during molecular beam epitaxial growth of Si layers for efficient 1.54 μm light emission. *Applied Physics Letters*, **1997**, 70, 3383-3385	3.4	36
294	Properties of Ga-interstitial defects in AlxGa1−xNyP1−y. *Physical Review B*, **2005**, 71,	3.3	36
293	On the origin of spin loss in GaMnN/InGaN light-emitting diodes. *Applied Physics Letters*, **2004**, 84, 2599-2601	3.4	35
292	Turning ZnO into an Efficient Energy Upconversion Material by Defect Engineering. *Advanced Functional Materials*, **2014**, 24, 3760-3764	15.6	32
291	Defects in N, O and N, Zn implanted ZnO bulk crystals. *Journal of Applied Physics*, **2013**, 113, 103509	2.5	31
290	Exciton spin relaxation in diluted magnetic semiconductor Zn1−xMnxSe/CdSe superlattices: Effect of spin splitting and role of longitudinal optical phonons. *Physical Review B*, **2003**, 67,	3.3	31

289	Temperature dependence of the GaNxP1−x band gap and effect of band crossover. *Applied Physics Letters*, **2002**, 81, 3984-3986	3.4	31
288	Evidence for coupling between exciton emissions and surface plasmon in Ni-coated ZnO nanowires. *Nanotechnology*, **2012**, 23, 425201	3.4	30
287	Growth and characterization of dilute nitride GaNxP1−x nanowires and GaNxP1−x/GaNyP1−y core/shell nanowires on Si (111) by gas source molecular beam epitaxy. *Applied Physics Letters*, **2014**, 105, 072107	3.4	29
286	Efficient room-temperature nuclear spin hyperpolarization of a defect atom in a semiconductor. *Nature Communications*, **2013**, 4, 1751	17.4	29
285	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. *Applied Physics Letters*, **2002**, 81, 2196-2198	3.4	29
284	Room-temperature InP/InAsP Quantum Discs-in-Nanowire Infrared Photodetectors. *Nano Letters*, **2017**, 17, 3356-3362	11.5	28
283	Spin injection and helicity control of surface spin photocurrent in a three dimensional topological insulator. *Nature Communications*, **2017**, 8, 15401	17.4	27
282	Suppression of non-radiative surface recombination by N incorporation in GaAs/GaNAs core/shell nanowires. *Scientific Reports*, **2015**, 5, 11653	4.9	27
281	Mechanism for radiative recombination and defect properties of GaP/GaNP core/shell nanowires. *Applied Physics Letters*, **2012**, 101, 163106	3.4	27
280	Long lifetime of free excitons in ZnO tetrapod structures. *Applied Physics Letters*, **2010**, 96, 083104	3.4	26
279	The excitonic bandgap of GaN: Dependence on substrate. *Solid-State Electronics*, **1997**, 41, 239-241	1.7	26
278	Defects in dilute nitrides. *Journal of Physics Condensed Matter*, **2004**, 16, S3027-S3035	1.8	26
277	Optical characterization of III-nitrides. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2002**, 93, 112-122	3.1	26
276	Magnetizing lead-free halide double perovskites. *Science Advances*, **2020**, 6,	14.3	25
275	Electron spin filtering by thin GaNAs/GaAs multiquantum wells. *Applied Physics Letters*, **2010**, 96, 052104	3.4	25
274	Mechanism for thermal quenching of luminescence in SiGe/Si structures grown by molecular beam epitaxy: Role of nonradiative defects. *Applied Physics Letters*, **1997**, 71, 3676-3678	3.4	25
273	Experimental evidence for N-induced strong coupling of host conduction band states in GaNxP1−x: Insight into the dominant mechanism for giant band-gap bowing. *Physical Review B*, **2004**, 69,	3.3	25
272	Identification of a dominant mechanism for optical spin injection from a diluted magnetic semiconductor: Spin-conserving energy transfer via localized excitations. *Physical Review B*, **2005**, 72,	3.3	25

271	Origin of radiative recombination and manifestations of localization effects in GaAs/GaNAs core/shell nanowires. *Applied Physics Letters*, **2014**, 105, 253106	3.4	24
270	Mechanism for radiative recombination in ZnCdO alloys. *Applied Physics Letters*, **2007**, 90, 261907	3.4	23
269	Efficient spin depolarization in ZnCdSe spin detector: an important factor limiting optical spin injection efficiency in ZnMnSe/ZnCdSe spin light-emitting structures. *Applied Physics Letters*, **2004**, 85, 5260-5262	3.4	23
268	Structural properties of a GaNxP1−x alloy: Raman studies. *Applied Physics Letters*, **2001**, 78, 3959-3961	3.4	23
267	Energy upconversion in GaP/GaNP core/shell nanowires for enhanced near-infrared light harvesting. *Small*, **2014**, 10, 4403-8	11	22
266	Dynamics of exciton-spin injection, transfer, and relaxation in self-assembled quantum dots of CdSe coupled with a diluted magnetic semiconductor layer of Zn0.80Mn0.20Se. *Physical Review B*, **2007**, 75,	3.3	22
265	Enhancement of polymer endurance to UV light by incorporation of semiconductor nanoparticles. *Nanoscale Research Letters*, **2015**, 10, 81	5	21
264	Room-temperature electron spin amplifier based on Ga(In)NAs alloys. *Advanced Materials*, **2013**, 25, 738-42	21	21
263	Efficient upconversion of photoluminescence via two-photon absorption in bulk and nanorod ZnO. *Applied Physics B: Lasers and Optics*, **2012**, 108, 919-924	1.9	21
262	Effects of hydrogen on the optical properties of ZnCdO/ZnO quantum wells grown by molecular beam epitaxy. *Applied Physics Letters*, **2008**, 92, 261912	3.4	21
261	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaNxP1−x alloys: A proof for a general property of dilute nitrides. *Physical Review B*, **2004**, 70,	3.3	21
260	Point defects in dilute nitride III-N-As and III-N-P. *Physica B: Condensed Matter*, **2006**, 376-377, 545-551	2.8	20
259	Control of spin functionality in ZnMnSe-based structures: Spin switching versus spin alignment. *Applied Physics Letters*, **2003**, 82, 1700-1702	3.4	20
258	Strongly polarized quantum-dot-like light emitters embedded in GaAs/GaNAs core/shell nanowires. *Nanoscale*, **2016**, 8, 15939-47	7.7	19
257	Paramagnetic centers in detonation nanodiamonds studied by CW and pulse EPR. *Chemical Physics Letters*, **2010**, 493, 319-322	2.5	19
256	As-Grown 4H-SiC Epilayers with Magnetic Properties. *Materials Science Forum*, **2004**, 457-460, 747-750	0.4	19
255	Charge Generation via Relaxed Charge-Transfer States in Organic Photovoltaics by an Energy-Disorder-Driven Entropy Gain. *Journal of Physical Chemistry C*, **2018**, 122, 12640-12646	3.8	19
254	Raman spectroscopy of GaP/GaNP core/shell nanowires. *Applied Physics Letters*, **2014**, 105, 193102	3.4	18

253	Identification of Ga-interstitial defects in GaNyP1y and AlxGa1xNyP1y. *Physical Review B*, **2004**, 70,	3.3	18
252	Intrinsic Doping: A New Approach for n-Type Modulation Doping in InP-Based Heterostructures. *Physical Review Letters*, **1996**, 77, 2734-2737	7.4	18
251	Near-Infrared Lasing at 1 m from a Dilute-Nitride-Based Multishell Nanowire. *Nano Letters*, **2019**, 19, 885-890	11.5	18
250	Origin of strong photoluminescence polarization in GaNP nanowires. *Nano Letters*, **2014**, 14, 5264-9	11.5	17
249	Efficient nitrogen incorporation in ZnO nanowires. *Scientific Reports*, **2015**, 5, 13406	4.9	17
248	Catalytic conversion of C2-C3 alcohols on detonation nanodiamond and its modifications. *Russian Journal of Physical Chemistry A*, **2012**, 86, 26-31	0.7	17
247	Effects of defect scattering on the photoluminescence of exciton-polaritons in n-GaN. *Solid State Communications*, **1998**, 105, 497-501	1.6	17
246	Dominant factors limiting efficiency of optical spin detection in ZnO-based materials. *Applied Physics Letters*, **2008**, 92, 092103	3.4	17
245	Effects of stoichiometry on defect formation in ZnO epilayers grown by molecular-beam epitaxy: An optically detected magnetic resonance study. *Journal of Applied Physics*, **2008**, 103, 023712	2.5	17
244	Efficient spin relaxation in InGaNGaN and InGaNGaMnN quantum wells: An obstacle to spin detection. *Applied Physics Letters*, **2005**, 87, 192107	3.4	17
243	Photoluminescence of the two-dimensional hole gas in p-type delta -doped Si layers. *Physical Review B*, **1996**, 53, 9587-9590	3.3	17
242	Near-Infrared Light-Responsive Cu-Doped Cs2AgBiBr6. *Advanced Functional Materials*, **2020**, 30, 2005521	15.6	17
241	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. *Nano Letters*, **2015**, 15, 4052-8	11.5	16
240	Identification of an isolated arsenic antisite defect in GaAsBi. *Applied Physics Letters*, **2014**, 104, 052110	3.4	16
239	Optimizing GaNP coaxial nanowires for efficient light emission by controlling formation of surface and interfacial defects. *Nano Letters*, **2015**, 15, 242-7	11.5	15
238	Effects of Ni-coating on ZnO nanowires: A Raman scattering study. *Journal of Applied Physics*, **2013**, 113, 214302	2.5	15
237	Defect properties of ZnO nanowires revealed from an optically detected magnetic resonance study. *Nanotechnology*, **2013**, 24, 015701	3.4	15
236	Similarity between the 0.88-eV photoluminescence in GaN and the electron-capture emission of the OP donor in GaP. *Physical Review B*, **1998**, 58, R13351-R13354	3.3	15

235	Interfacial bonding in a CdS/PVA nanocomposite: A Raman scattering study. *Journal of Colloid and Interface Science*, **2015**, 452, 33-37	9.3	14
234	Dynamics of donor bound excitons in ZnO. *Applied Physics Letters*, **2013**, 102, 121103	3.4	14
233	Strong room-temperature optical and spin polarization in InAs/GaAs quantum dot structures. *Applied Physics Letters*, **2011**, 98, 203110	3.4	14
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231	Efficiency of optical spin injection and spin loss from a diluted magnetic semiconductor ZnMnSe to CdSe nonmagnetic quantum dots. *Physical Review B*, **2008**, 77,	3.3	14
230	Optical study of spin injection dynamics in InGaN□GaN quantum wells with GaMnN injection layers. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2668		14
229	Formation of Ga interstitials in (Al,In)yGa1□NxP1□ alloys and their role in carrier recombination. *Applied Physics Letters*, **2004**, 85, 2827-2829	3.4	14
228	Optical properties of GaNAs/GaAs structures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 143-147	3.1	14
227	Exciton properties in p-type GaAs/AlxGa1-xAs quantum wells in the high doping regime. *Physical Review B*, **1996**, 54, 16989-16993	3.3	14
226	Identification of Grown-In Efficient Nonradiative Recombination Centers in Molecular Beam Epitaxial Silicon. *Physical Review Letters*, **1996**, 77, 4214-4217	7.4	14
225	Influence of ion bombardment on Si and SiGe films during molecular beam epitaxy growth. *Applied Physics Letters*, **1996**, 68, 238-240	3.4	14
224	Vibronic coherence contributes to photocurrent generation in organic semiconductor heterojunction diodes. *Nature Communications*, **2020**, 11, 617	17.4	14
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222	Optical characterization of ZnMnO-based dilute magnetic semiconductor structures. *Journal of Vacuum Science & Technology B*, **2006**, 24, 259		13
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220	Effect of momentum relaxation on exciton spin dynamics in diluted magnetic semiconductor ZnMnSe□CdSe superlattices. *Physical Review B*, **2005**, 71,	3.3	13
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218	Spin injection in lateral InAs quantum dot structures by optical orientation spectroscopy. *Nanotechnology*, **2009**, 20, 375401	3.4	12

217	Slowdown of light due to exciton-polariton propagation in ZnO. *Physical Review B*, **2011**, 83,	3.3	12
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215	Modeling of band gap properties of GaInNP alloys lattice matched to GaAs. *Applied Physics Letters*, **2006**, 88, 031907	3.4	12
214	Room-temperature polarized spin-photon interface based on a semiconductor nanodisk-in-nanopillar structure driven by few defects. *Nature Communications*, **2018**, 9, 3575	17.4	12
213	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsP-InP Core-Shell Nanowires. *Nano Letters*, **2019**, 19, 2674-2681	11.5	11
212	Effects of Ultraviolet Light on Optical Properties of Colloidal CdS Nanoparticles Embedded in Polyvinyl Alcohol (PVA) Matrix. *Advanced Science, Engineering and Medicine*, **2012**, 4, 394-400	0.6	11
211	On the origin of suppression of free exciton no-phonon emission in ZnO tetrapods. *Applied Physics Letters*, **2010**, 96, 033108	3.4	11
210	Strong effects of carrier concentration on the Fermi-edge singularity in modulation-doped InP/InxGa1⊠As heterostructures. *Physical Review B*, **1997**, 55, 7052-7058	3.3	11
209	Photoluminescence characterization of GaNAs/GaAs structures grown by molecular beam epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 75, 166-169	3.1	11
208	Growth of isotopically enriched ZnO nanorods of excellent optical quality. *Journal of Crystal Growth* , **2015**, 429, 6-12	1.6	10
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206	Fabry-Perot Microcavity Modes in Single GaP/GaNP Core/Shell Nanowires. *Small*, **2015**, 11, 6331-7	11	10
205	Anomalous spectral dependence of optical polarization and its impact on spin detection in InGaAs/GaAs quantum dots. *Applied Physics Letters*, **2014**, 105, 132106	3.4	10
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200	Magneto-optical studies of the 0.88-eV photoluminescence emission in electron-irradiated GaN. *Physical Review B*, **2000**, 62, 16572-16577	3.3	10

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198	Effects of Nitrogen Incorporation on Structural and Optical Properties of GaNAsP Nanowires. *Journal of Physical Chemistry C*, **2017**, 121, 7047-7055	3.8	9
197	Recharging behavior of nitrogen-centers in ZnO. *Journal of Applied Physics*, **2014**, 116, 063701	2.5	9
196	Efficient room-temperature spin detector based on GaNAs. *Journal of Applied Physics*, **2012**, 111, 07C303	2.5	9
195	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. *Thin Solid Films*, **2013**, 543, 11-15	2.2	9
194	Optically detected magnetic resonance studies of point defects in quaternary GaNAsP epilayers grown by vapor phase epitaxy. *Applied Physics Letters*, **2013**, 102, 021910	3.4	9
193	Optically detected magnetic resonance studies of point defects in Ga(Al)NAs. *Physical Review B*, **2006**, 73,	3.3	9
192	Optical characterization of wide bandgap semiconductors. *Thin Solid Films*, **2000**, 364, 98-106	2.2	9
191	Thermally activated intersubband and hopping transport in center-doped p-type GaAs/AlxGa1-xAs quantum wells. *Physical Review B*, **1996**, 53, 1357-1361	3.3	9
190	Optical detection of quantum oscillations in InP/InGaAs quantum structures. *Applied Physics Letters*, **1996**, 69, 809-811	3.4	9
189	Coexistence of two deep donor states, DX- and DX0, of the Sn donor in Ga1-xAlxAs. *Physical Review B*, **1992**, 45, 11667-11671	3.3	9
188	Luminescent and Optically Detected Magnetic Resonance Studies of CdS/PVA Nanocomposite. *Nanoscale Research Letters*, **2017**, 12, 130	5	8
187	Effects of N implantation on defect formation in ZnO nanowires. *Thin Solid Films*, **2019**, 687, 137449	2.2	8
186	Effects of Ga doping on optical and structural properties of ZnO epilayers. *Superlattices and Microstructures*, **2009**, 45, 413-420	2.8	8
185	Density-dependent dynamics of exciton magnetic polarons in ZnMnSe/ZnSSe type-II quantum wells. *Physical Review B*, **2006**, 73,	3.3	8
184	Radiative recombination of GaInNP alloys lattice matched to GaAs. *Applied Physics Letters*, **2006**, 88, 011910	3.4	8
183	Optical and electrical characterization of (Ga,Mn)N/InGaN multiquantum well light-emitting diodes. *Journal of Electronic Materials*, **2004**, 33, 467-471	1.9	8
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178	Properties of deep photoluminescence bands in SiGe/Si quantum structures grown by molecular beam epitaxy. *Applied Physics Letters*, **1995**, 67, 1642-1644	3.4	8
177	Nonradiative defects in Si and SiGe/Si heterostructures grown by molecular beam epitaxy. *Applied Physics Letters*, **1996**, 68, 1256-1258	3.4	8
176	Magneto-optical properties of Cr3+ in □Ga2O3. *Applied Physics Letters*, **2021**, 119, 052101	3.4	8
175	Thermal-annealing effects on energy level alignment at organic heterojunctions and corresponding voltage losses in all-polymer solar cells. *Nano Energy*, **2020**, 72, 104677	17.1	7
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173	Effect of exciton transfer on recombination dynamics in vertically nonuniform GaAsSb epilayers. *Applied Physics Letters*, **2019**, 114, 252101	3.4	7
172	Donor bound excitons involving a hole from the B valence band in ZnO: Time resolved and magneto-photoluminescence studies. *Applied Physics Letters*, **2011**, 99, 091909	3.4	7
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169	Effect of postgrowth hydrogen treatment on defects in GaNP. *Applied Physics Letters*, **2011**, 98, 141920	3.4	7
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167	Postgrowth hydrogen treatments of nonradiative defects in low-temperature molecular beam epitaxial Si. *Applied Physics Letters*, **1997**, 70, 369-371	3.4	7
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165	Evaluation of optical quality and defect properties of GaNxP1□ alloys lattice matched to Si. *Applied Physics Letters*, **2004**, 85, 6347-6349	3.4	7
164	Effects of rapid thermal annealing on optical properties of GaNxP1□alloys grown by solid source molecular beam epitaxy. *Semiconductor Science and Technology*, **2005**, 20, 353-356	1.8	7

163	Nature and Formation of Non-Radiative Defects in GaNAs And InGaAsN. *Materials Research Society Symposia Proceedings*, **2001**, 692, 1		7
162	Properties of Er-related emission in in situ doped Si epilayers grown by molecular beam epitaxy. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 1732		7
161	Photoluminescence of defects induced in silicon by SF6/O2 reactive-ion etching. *Journal of Applied Physics*, **1995**, 78, 3348-3352	2.5	7
160	Effect of hydrogen passivation on Be-doped AlGaAs/GaAs quantum wells. *Applied Physics Letters*, **1996**, 68, 1365-1367	3.4	7
159	Room-temperature electron spin polarization exceeding 90% in an opto-spintronic semiconductor nanostructure via remote spin filtering. *Nature Photonics*,	33.9	7
158	Dilute nitrides-based nanowires-a promising platform for nanoscale photonics and energy technology. *Nanotechnology*, **2019**, 30, 292002	3.4	6
157	Understanding and optimizing spin injection in self-assembled InAs/GaAs quantum-dot molecular structures. *Nano Research*, **2016**, 9, 602-611	10	6
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154	Effects of P implantation and post-implantation annealing on defect formation in ZnO. *Journal of Applied Physics*, **2012**, 111, 043520	2.5	6
153	Metamorphic InGaAs quantum wells for light emission at 1.31.6 m. *Thin Solid Films*, **2007**, 515, 4348-4351	2.2	6
152	Hydrogen passivation of nitrogen in GaNAs and GaNP alloys: How many H atoms are required for each N atom?. *Applied Physics Letters*, **2007**, 90, 021920	3.4	6
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150	Temperature behavior of the GaNP band gap energy. *Solid-State Electronics*, **2003**, 47, 493-496	1.7	6
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